

New Jersey Semi-Conductor Products, Inc.

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N-Channel MOSFET Transistor

IRF9540

FEATURES

- Drain Current $-I_D = -19A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = -100V$ (Min)
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.2 \Omega$ (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

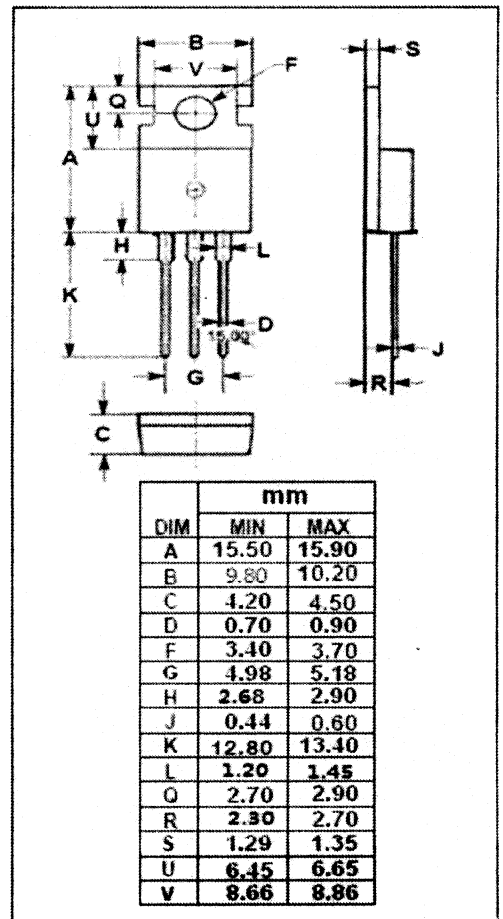
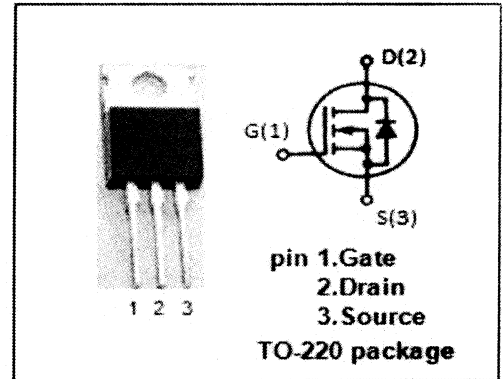
- motor drive, DC-DC converter, power switch and solenoid drive.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	-19	A
$I_{D(st)}$	Drain Current-Single Pulse	-76	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	150	W
T_J	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Thermal Resistance, Junction to Case	0.83	$^\circ C/W$



Quality Semi-Conductors

ELECTRICAL CHARACTERISTICS

$T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=-1\text{mA}$	-100	--	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=-10\text{V}; I_D=-0.25\text{mA}$	-2	-4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=-10\text{V}; I_D=-9.5\text{A}$	--	0.2	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$	--	± 0.1	μA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-100\text{V}; V_{GS}=0$	--	-25	μA
V_{SD}	Forward On-Voltage	$I_S=-19\text{A}; V_{GS}=0$	--	-1.5	V